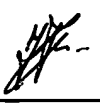


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	BH		<del>Lu, N.C.C. et al., "A Buried Trench DRAM Cell Using a Self-Aligned Epitaxy Over Trench Technology", IEDM Tech. Digest, 1988, pp. 568-591.</del>		
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EXAMINER <i>J. Mondt</i>			DATE CONSIDERED <i>09/07/05</i>				
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January 14, 2004GROUP  
Unknown

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Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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UP	AA	6,429,085 B1	08/02	Plinter			
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